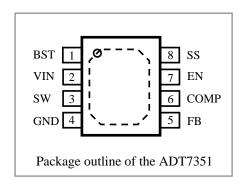


General Description

The ADT7351 is a step-down converter with integrated switching MOSFET. It operates wide input supply voltage range from 4.5V to 28V with 3A continuous output current. It includes current limiting protection and thermal shutdown.

It reduces design complexity and external component count. The ADT7351 is available in small outline SOIC-8(with Exposed pad) package.



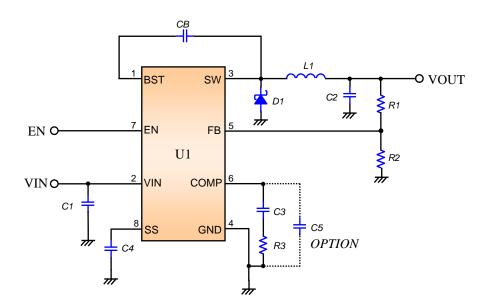
Features

- Current mode buck regulator with 925KHz fixed frequency
- Input voltage range: 4.5V to 28V
- Adjustable output range: 0.92V to 21V
- Continuous output current : 3A
- Integrated Power MOSFET switch : 100mΩ
- Under Voltage Lockout
- Thermal shutdown & current limit protection

Applications

- Distributed Power Systems
- Battery charger
- Pre-regulator for Linear regulators
- Set-top boxes (STB)
- Cigarette Lighter powered devices.

Typical Application Circuit



^{*} This specifications are subject to be changed without notice



Part List

Component	Туре	Value (Model)	Manufacturer
U1	IC	ADT7351	ADTech
D1	Schottky Barrier Diode	B330A	DIODES
L1	Chip inductor	4.7uH / 3.6A	TDK
C1	MLCC	10μF / 50V	-
C2	MLCC	47μF / 6.3V	-
C3	MLCC	5.6nF	-
C4	MLCC	100 nF	-
СВ	MLCC	10nF	-
R1	Chip resistor	26.5kΩ / 1%	-
R2	Chip resistor	10kΩ / 1%	-
R3	Chip resistor	15kΩ / 1%	-

Pin Description

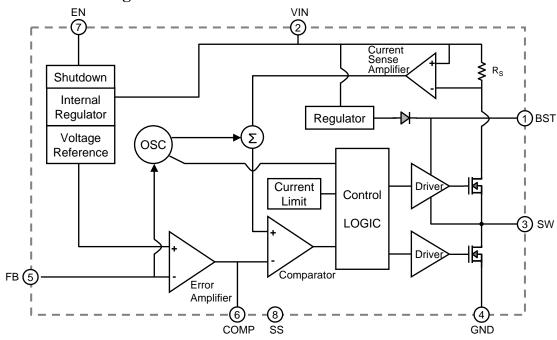
Pin No.	Name	I/O	Туре	Description
1	BST	I	A	Bootstrap capacitor connection
2	VIN	I	P	Power supply input
3	SW	0	D	Switching node connection
4	GND	-	G	Ground
5	FB	I	A	Feedback voltage input
6	COMP	0	A	Compensation node
7	EN	I	A	Chip enable input
8	SS	0	A	Soft start node

I : Input pin O : Output pin IO : Input/Output pin

P: Power pin G: Ground pin A: Analog pin D: Digital pin



Functional Block Diagram



Absolute Maximum Ratings (Note1)

Parameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage	V _{IN}	-0.3	-	30	V
SW pin voltage	V_{SW}	-0.5	-	$V_{IN} + 0.3$	V
BST pin voltage	V _{BST}	$V_{SW} - 0.3$	-	V _{SW} + 6	V
All Other Pins	-	-0.3	-	+6	V
Max. power dissipation (Ta=25°C) (Note2)	P_{D}	-	-	2.08	W
Thermal resistance (Note3)	Θ_{JA}	-	60	-	°C/W
Storage temperature	T _{STG}	-65	-	+150	°C
Junction temperature	$T_{J.MAX}$	-	-	+150	°C

Note1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

Note2. derate $17 \text{mW}/^{\circ}\text{C}$ above $+25 ^{\circ}\text{C}$. This is recommended to operate under this power dissipation specification.

Note3. Measured on JESD51-7, 4-layer PCB

Operating Ratings

Parameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage	V _{IN}	4.5	12.0	28.0	V
Output voltage	V _{OUT}	0.92	-	21	V
Operating temperature	T_{OPR}	-40	-	+85	$^{\circ}$
Junction temperature	T_{J}	-	-	+125	°

^{*} This specifications are subject to be changed without notice



Electrical Characteristics (Ta=25 $^{\circ}$ C, V_{IN}=12V, unless otherwise noted)

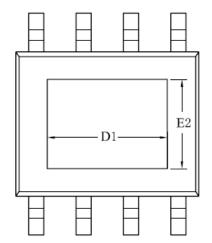
Parameters	Symbol	Condition	Min.	Тур.	Max.	Unit
Supply current (shutdown)	I_{OFF}	$V_{EN} = 0V$	-	20	-	μA
Supply current (quiescent)	I_Q	$V_{EN} = 3V, V_{FB} = 1.4V$	-	1.3	-	mA
Feedback voltage	V_{FB}	$4.5V \le V_{IN} \le 28V,$ $V_{COMP} < 2V$	0.89	0.92	0.95	V
Error Amplifier Voltage Gain	A _{EA}	$V_{FB} = 0.8V$	-	500	-	V/V
Error Amplifier Transconductance	G_{EA}	$\Delta I_{COMP} = \pm 10 \mu A$	-	900	-	μA/V
High-Side Switch On Resistance (Note5)	R _{ON.H}	-	-	100	-	mΩ
Low-Side Switch On Resistance (Note5)	R _{ON.L}	-	-	10	-	Ω
High-Side Switch Leakage Current		$V_{EN} = 0V$, $V_{SW} = 0V$	-	0.1	-	μA
Current Limit (Note5)		-	-	4.0	-	A
Oscillator frequency	F _{sw}	-	-	925	-	kHz
Fold-back frequency		$V_{FB} = 0V$	-	110	-	kHz
Maximum Duty cycle	D _{MAX}	-	-	85	-	%
Minimum On time	T_{ON}	-	-	100	-	ns
UVLO rising threshold		V _{IN} rising	-	2.6	-	V
UVLO threshold hysteresis		-	-	200	-	mV
EN threshold voltage		-	-	1.2	-	V
Enable pull-up current		$V_{EN} = 0V$	-	1.0	-	μA
Soft-Start Period		C4 = 100 nF	-	10	-	ms
Thermal shutdown (Note5)		-	-	145	-	°C

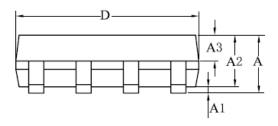
Note5. guaranteed by design.

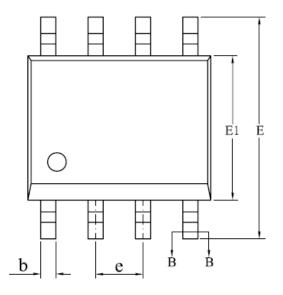
^{*} This specifications are subject to be changed without notice



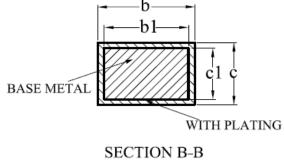
Package; SOIC-8 with exposed pad, 4.9mm x 3.94mm body (units:mm)

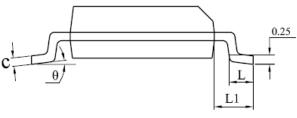






	MILLIMETER				
SYMBOL	MIN	NOM	MAX		
A		_	1.77		
A1	0.08	0.18	0.28		
A2	1.20	1.40	1.60		
A3	0.55	0.65	0.75		
b	0.39	_	0.48		
b1	0.38	0.41	0.43		
с	0.21	_	0.26		
c1	0.19	0.20	0.21		
D	4.70	4.90	5.10		
Е	5.80	6.00	6.20		
E1	3.70	3.90	4.10		
e	1.27BSC				
L	0.50	0.65	0.80		
L1	1.05BSC				
θ	0		8°		
D1	3.30REF				
E2	2.40REF				





 $^{* \}textit{This specifications are subject to be changed without notice}$